40 Watt Peak Power Zener Surge Protection Device

SC-70 Dual Common Cathode Zeners

MMBZ27VCW

These dual monolithic silicon zener diodes are designed for applications requiring transient overvoltage protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. Their dual junction common cathode design protects two separate lines using only one package. These devices are ideal for situations where board space is at a premium.

Specification Features:

- SC-70 Package Allows Either Two Separate Unidirectional Configurations or a Single Bidirectional Configuration
- Working Peak Reverse Voltage Range 22 V
- Standard Zener Breakdown Voltage 27 V
- Peak Power 40 W @ 1.0 ms (Bidirectional), per Figure 4 Waveform
- ESD Rating of Class N (exceeding 16 kV) per the Human Body Model
- Low Leakage < 100 nA
- Flammability Rating: UL 94 V-O
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Mechanical Characteristics:

CASE: Void-free, transfer-molded, thermosetting plastic case

FINISH: Corrosion resistant finish, easily solderable

MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:

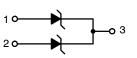
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260°C for 10 Seconds



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PIN 1. ANODE 2. ANODE 3. CATHODE



SC-70 CASE 419 STYLE 4





AC = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBZ27VCWT1G	SC-70 (Pb-Free)	3000 / Tape & Reel
SZMMBZ27VCWT1G	SC-70 (Pb-Free)	3000 / Tape & Reel
MMBZ27VCWT3G	SC-70 (Pb-Free)	10000 / Tape & Reel
SZMMBZ27VCWT3G	SC-70 (Pb-Free)	10000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation @ 1.0 ms (Note 1) @ $T_L \le 25^{\circ}C$	P_{pk}	40	Watts
Total Power Dissipation on FR-5 Board (Note 2) @ T _A = 25°C Derate above 25°C	P _D	200 1.6	mW mW/°C
Thermal Resistance Junction-to-Ambient	$R_{ heta JA}$	618	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	– 55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

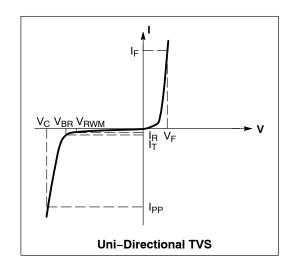
- 1. Nonrepetitive current pulse per Figure 4 and derate above $T_A = 25^{\circ}C$ per Figure 5.
- 2. $FR-5 = 1.0 \times 0.75 \times 0.62$ in.

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or 2 and 3)

Symbol	Parameter					
I _{PP}	Maximum Reverse Peak Pulse Current					
V _C	Clamping Voltage @ I _{PP}					
V _{RWM}	Working Peak Reverse Voltage					
I _R	Maximum Reverse Leakage Current @ V _{RWM}					
V _{BR}	Breakdown Voltage @ I _T					
I _T	Test Current					
V _{BR}	Maximum Temperature Coefficient of V _{BR}					
I _F	Forward Current					
V _F	Forward Voltage @ I _F					



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) **UNIDIRECTIONAL** (Circuit tied to Pins 1 and 3 or Pins 2 and 3)

 $(V_F = 1.1 \text{ V Max } @ I_F = 200 \text{ mA})$

				Breakdown Voltage			V _C @ I _{PP} (Note 4)			
	Device	V _{RWM}	I _R @ V _{RWM}	V _{BI}	V _{BR} (Note 3) (V)		@ I _T	V _C	I _{PP}	V_{BR}
Device	Marking	Volts	nA	Min	Nom	Max	mA	V	Α	mV/°C
MMBZ27VCWT1G, SZMMBZ27VCWT1G, MMBZ27VCWT3G, SZMMBZ27VCWT3G	AC	22	50	25.65	27	28.35	1.0	38	1.0	26

- 3. V_{BR} measured at pulse test current I_T at an ambient temperature of 25°C.
- 4. Surge current waveform per Figure 4 and derate per Figure 5

TYPICAL CHARACTERISTICS

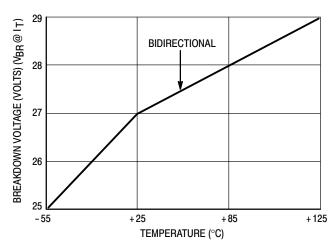


Figure 1. Typical Breakdown Voltage versus Temperature

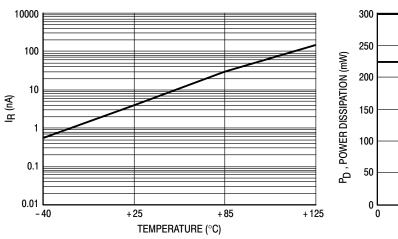


Figure 2. Typical Leakage Current versus Temperature

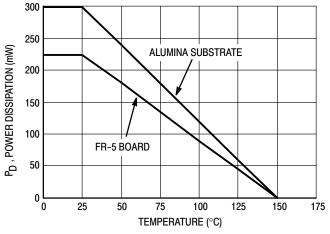


Figure 3. Steady State Power Derating Curve

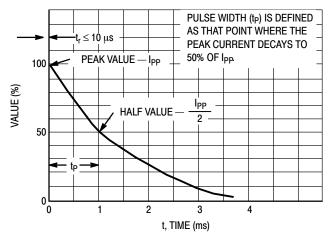


Figure 4. Pulse Waveform

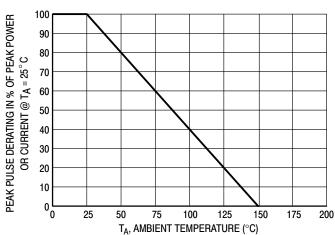


Figure 5. Pulse Derating Curve

TYPICAL APPLICATIONS

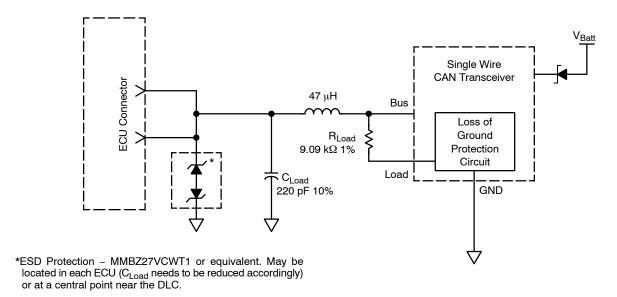
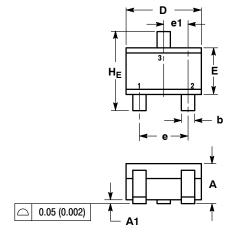


Figure 6. Single Wire CAN Network

Figure is the recommended solution for transient EMI/ESD protection. This circuit is shown in the Society of Automotive Engineers February, 2000 J2411 "Single Wire CAN Network for Vehicle Applications" specification (Figure 6, page 11). Note: the dual common anode zener configuration shown above is electrically equivalent to a dual common cathode zener configuration.

PACKAGE DIMENSIONS

SC-70 (SOT-323) CASE 419-04 ISSUE N





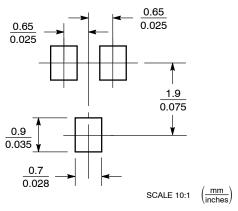
IOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.80	0.90	1.00	0.032	0.035	0.040	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
A2	0.70 REF			0.028 REF			
b	0.30	0.35	0.40	0.012	0.014	0.016	
С	0.10	0.18	0.25	0.004	0.007	0.010	
D	1.80	2.10	2.20	0.071	0.083	0.087	
E	1.15	1.24	1.35	0.045	0.049	0.053	
е	1.20	1.30	1.40	0.047	0.051	0.055	
e1	0.65 BSC			0.026 BSC			
L	0.20	0.38	0.56	0.008	0.015	0.022	
HE	2.00	2.10	2.40	0.079	0.083	0.095	

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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